

# GaAs integrated power amplifier

## O242SM4

### Features

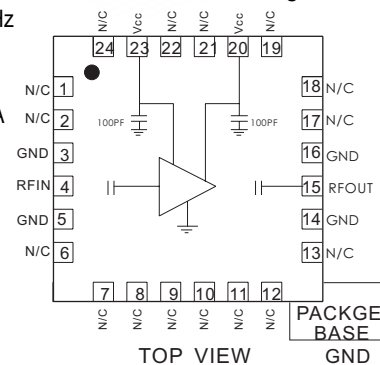
- Working frequency band: 2.2~3.5GHz
- Psat output power: 29dBm
- Gain: 22dB
- Single-supply operation: +5V@210mA
- Input/Output Impedance: 50 Ohm
- Package Size: 4.0 x 4.0 x 1.0mm

### Application

Suitable for a variety of applications:

- Microwave radio
- Military and aerospace
- Test and measurement
- Instruments apparatuses
- RF/Microwave circuit

### Functional block diagram



### Overview

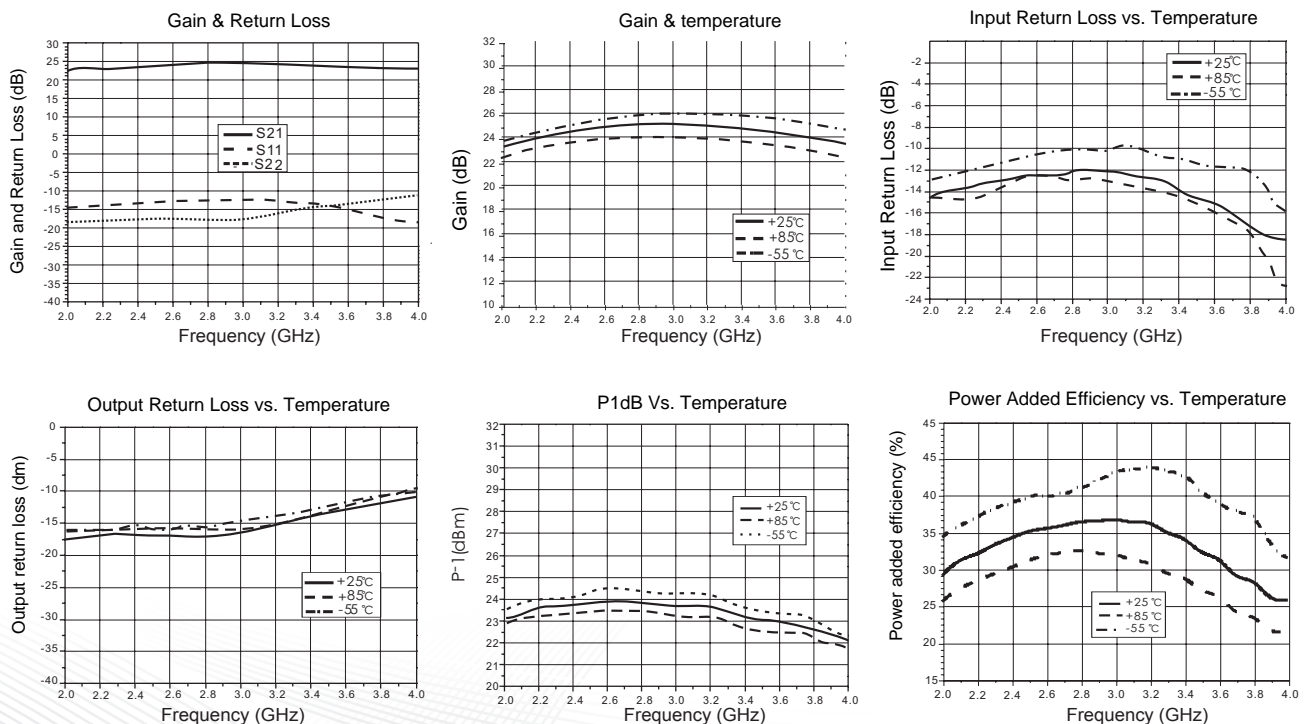
The O242SM4 is a 2.2-3.5GHz power amplifier that operates from a single supply and provides 23dB of gain and 25dBm of saturated output power at an operating voltage of +5V.

The amplifier uses a 4x4mm surface-mount non-leaded ceramic package for hermetic encapsulation. The pin pad surface is gold-plated and suitable for reflow soldering.

### Electrical Characteristics (T<sub>A</sub> = +25°C, 50Ω system)

Parameter		Min.	Typ.	Max.	Unit
Frequency band		2.2-3.5			GHz
+5V	Gain		23		dB
	Saturated output power (Psat)	24	25	—	dBm
	Input/output return loss	10	12	—	dB
	Working current	—	230	—	mA

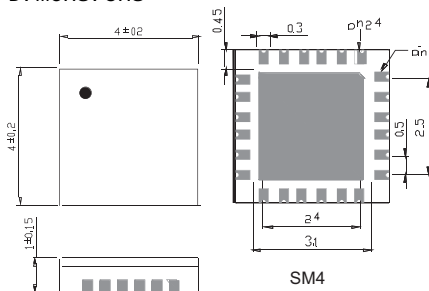
### Test



## Pin definition

Pin.NO	Pin Name	Description
4	RF in	RF signal, external 50 ohm system, no need to block straight
15	RF out	RF signal, external 50 ohm system, no need to block straight
20, 23	VCC	Power port +5V
3, 5, 14, 16	GND	The ground pin and the bottom of the shell need a large area to ground
others	NC	Vacant

## Dimensions



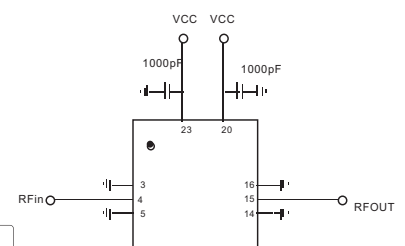
## Limit parameter

Supply voltage (V)	+10
RF input power (dBm)	+20
Junction temperature (°C)	175
Storage temperature (°C)	-65~+150
Working temperature (°C)	-55~+125



ELECTROSTATIC SENSITIVE DEVICE  
OBSERVE HANDLING PRECAUTIONS

## Application Information



## Description:

1. Unit: mm
2. Shell Material: Alumina Ceramics
- 3 pin surface plating: nickel gold
4. The shell surface warpage: less than 0.05mm
5. All ground pins please connect RF ground
6. This tube is suitable for reflow mounting process